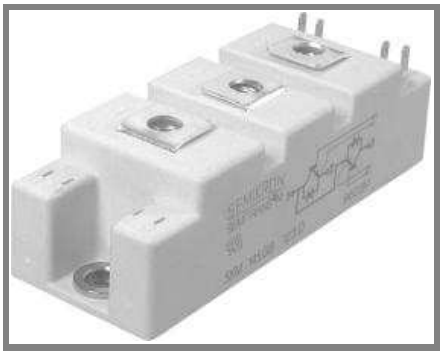
SKM 145GB066D



SEMITRANS® 2

Trench IGBT Modules

SKM 145GB066D

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications*

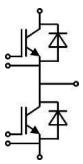
- AC inverter Drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to T_c = 125°C max, recomm. T_{op} = -40 ... +150°C, product rel. results valid for $T_j \leq 150°C$
- SC data: $t_p \leq 6$ s; VGE≤15V; T_j=150°C; $V_{cc} \leq 360V$, use of soft R_G necessary!
- Take care of over-voltage caused by stray induct.

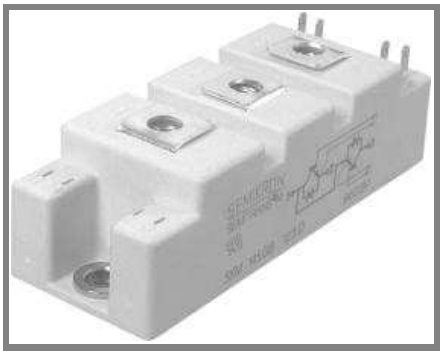
Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 175 °C	T_c = 25 °C	195	A
		T_c = 80 °C	150	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		300	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 360 V; $V_{GE} \leq$ 15 V; V_{CES} < 600 V	T_j = 150 °C	6	s
Inverse Diode				
I_F	T_j = 175 °C	T_c = 25 °C	150	A
		T_c = 80 °C	100	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		300	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 175 °C	880	A
Module				
$I_{t(RMS)}$			200	A
T_{vj}			- 40 ... + 175	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics	T_{case} = 25°C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2,4 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,08	0,25	mA
V_{CE0}		T_j = 25 °C		0,9	1	V
		T_j = 150 °C		0,85	0,9	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		3,7	6	mΩ
		T_j = 150°C		5,7	8	mΩ
$V_{CE(sat)}$	I_{Cnom} = 150 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,45	1,9	V
		T_j = 150°C$_{chiplev.}$		1,7	2,1	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		9,25		nF
C_{oes}				0,6		nF
C_{res}				0,28		nF
Q_G	V_{GE} = -8V...+15V			1100		nC
R_{Gint}	T_j = °C			2		Ω
$t_{d(on)}$	R_{Gon} = 4,3 Ω	V_{CC} = 300V		150		ns
t_r		I_C= 150A		52		ns
E_{on}		T_j = 150 °C		8,5		mJ
$t_{d(off)}$	R_{Goff} = 4,3 Ω	V_{GE} = -8/+15V		490		ns
t_f				46		ns
E_{off}				5,5		mJ
$R_{th(j-c)}$	per IGBT				0,3	K/W



GB

SKM 145GB066D



SEMITRANS® 2

Trench IGBT Modules

SKM 145GB066D

Features

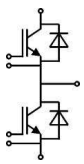
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications*

- AC inverter Drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to T_c = 125°C max, recomm. T_{op} = -40 ... +150°C, product rel. results valid for $T_j \leq 150°C$
- SC data: $t_p \leq 6$ s; VGE≤15V; T_j=150°C; $V_{cc} \leq 360V$, use of soft R_G necessary!
- Take care of over-voltage caused by stray induct.



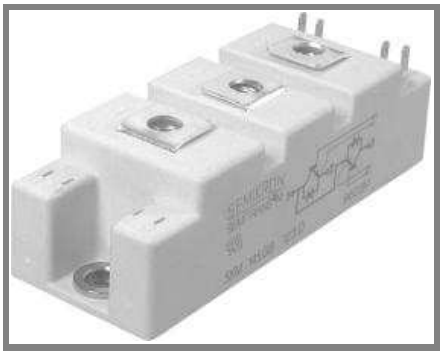
GB

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 150 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,4	1,6	V
		T_j = 150 °$C_{chiplev.}$				V
V_{F0}		T_j = 25 °C		0,95	1	V
r_F		T_j = 25 °C		3	4	mΩ
I_{RRM}	I_F = 150 A	T_j = 150 °C		90		A
Q_{rr}	di/dt = 2100 A/ s			20		C
E_{rr}	V_{GE} = -8 V; V_{CC} = 300 V			3,5		mJ
$R_{th(j-c)D}$	per diode				0,5	K/W
Module						
L_{CE}					30	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case}= 25 °C		0,75		mΩ
		T_{case}= 125 °C		1		mΩ
$R_{th(c-s)}$	per module				0,05	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M5		2,5		5	Nm
w					150	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

SKM 145GB066D



SEMITRANS® 2

Trench IGBT Modules

SKM 145GB066D

Features

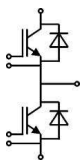
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications*

- AC inverter Drives
- UPS
- Electronic welders

Remarks

- Case temperature limited to T_c = 125°C max, recomm. T_{op} = -40 ... +150°C, product rel. results valid for $T_j \leq 150°C$
- SC data: $t_p \leq 6$ s; VGE≤15V; T_j=150°C; $V_{cc} \leq 360V$, use of soft R_G necessary!
- Take care of over-voltage caused by stray induct.



GB

Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	i = 1	220	mk/W
R_i	i = 2	60	mk/W
R_i	i = 3	16,5	mk/W
R_i	i = 4	3,5	mk/W
tau_i	i = 1	0,0447	s
tau_i	i = 2	0,0223	s
tau_i	i = 3	0,0015	s
tau_i	i = 4	0,0002	s
$Z_{th(j-c)D}$			
R_i	i = 1	330	mk/W
R_i	i = 2	137	mk/W
R_i	i = 3	28	mk/W
R_i	i = 4	5	mk/W
tau_i	i = 1	0,05	s
tau_i	i = 2	0,0129	s
tau_i	i = 3	0,002	s
tau_i	i = 4	0,0002	s

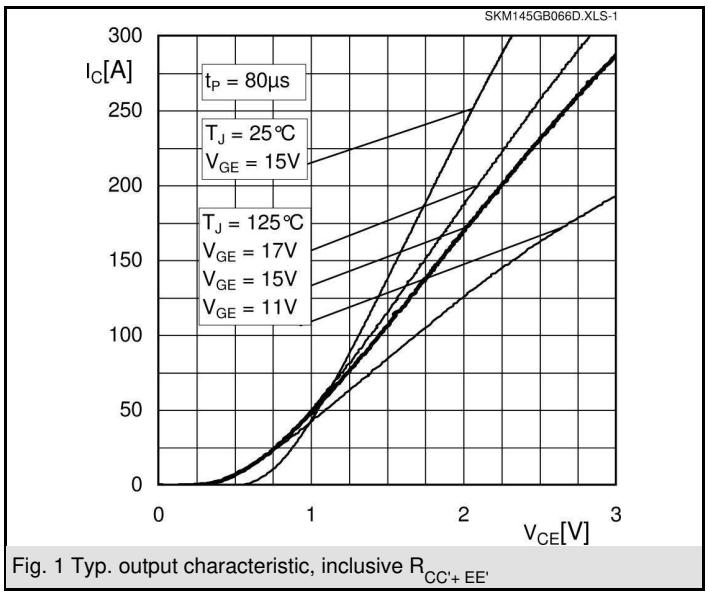


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

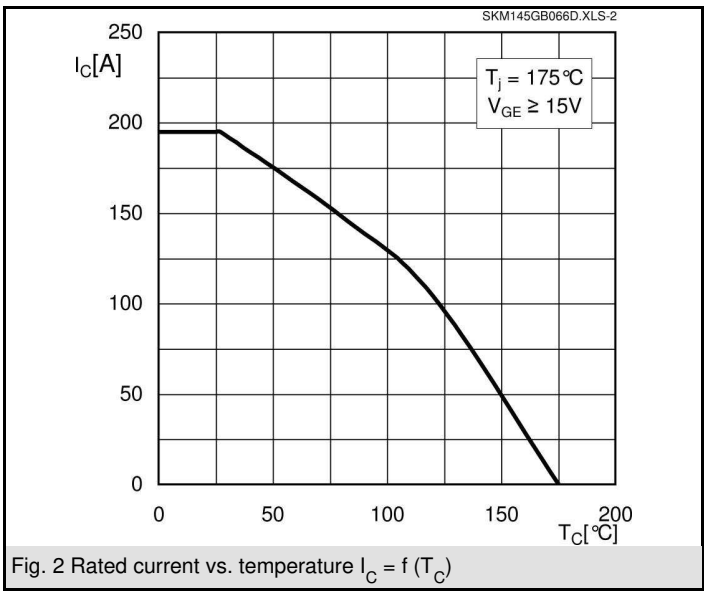


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

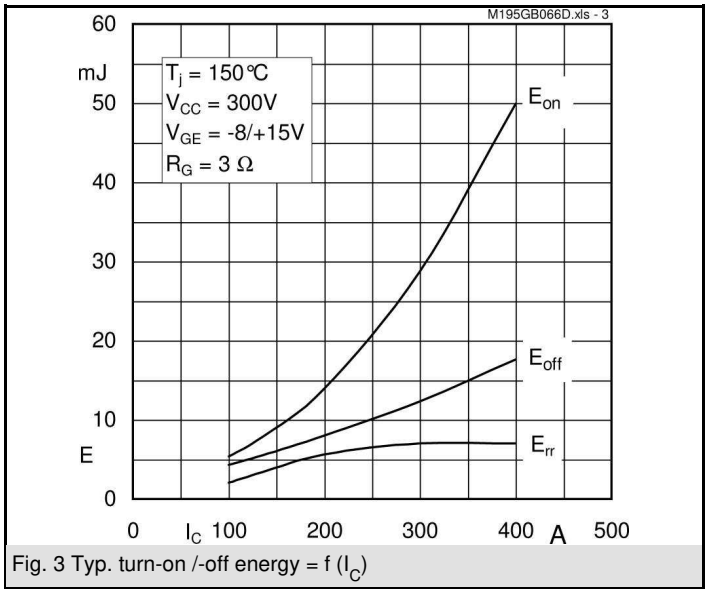


Fig. 3 Typ. turn-on /-off energy = f (I_C)

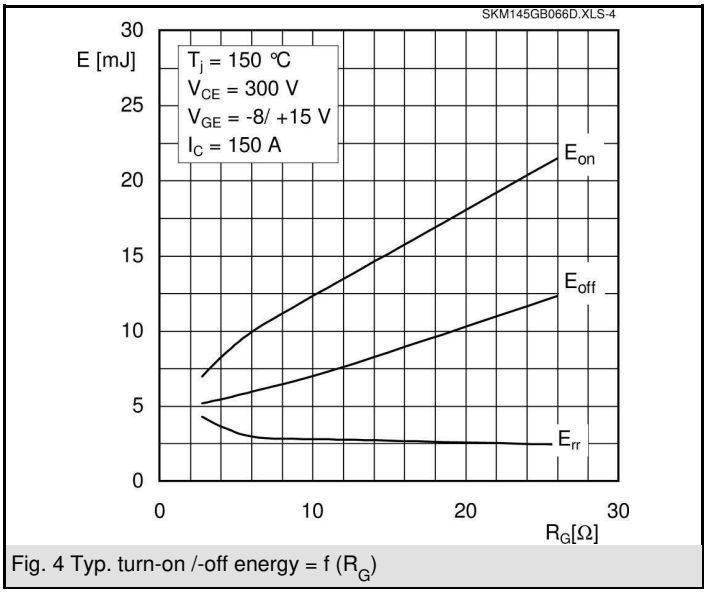


Fig. 4 Typ. turn-on /-off energy = f (R_G)

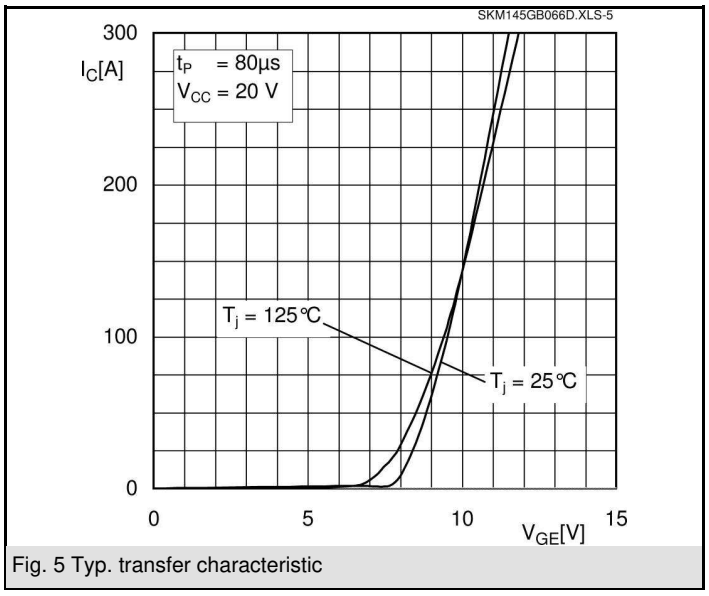


Fig. 5 Typ. transfer characteristic

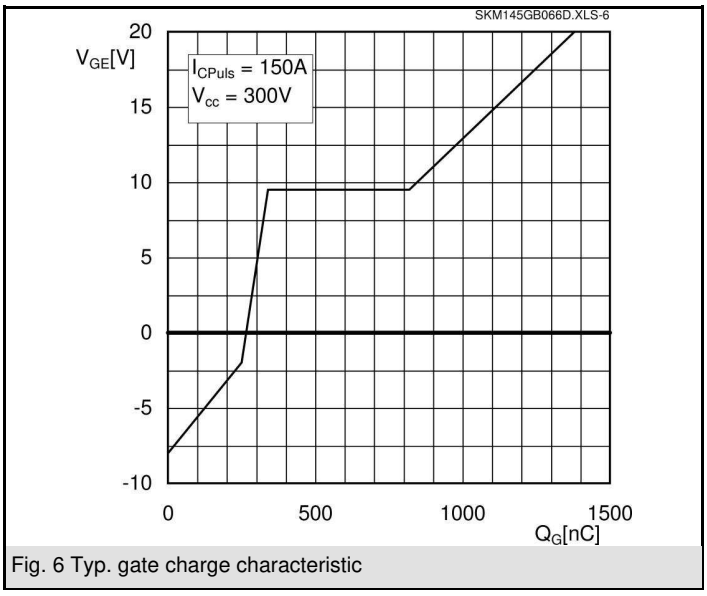


Fig. 6 Typ. gate charge characteristic

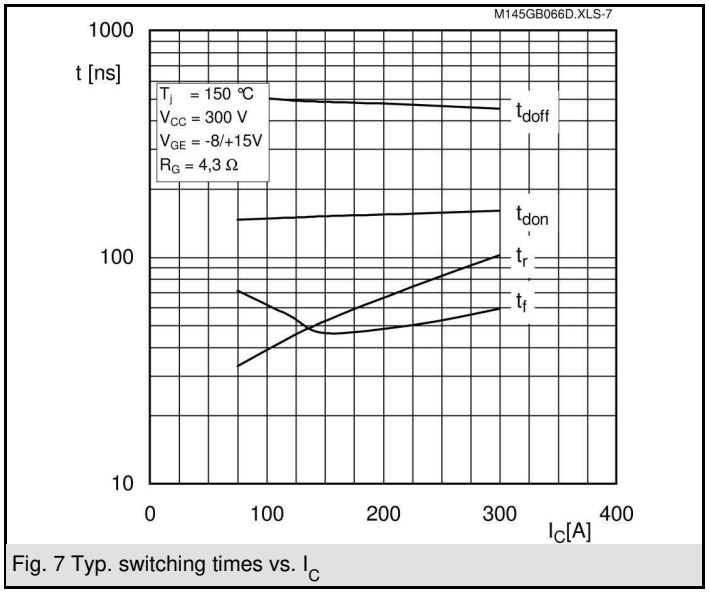


Fig. 7 Typ. switching times vs. I_C

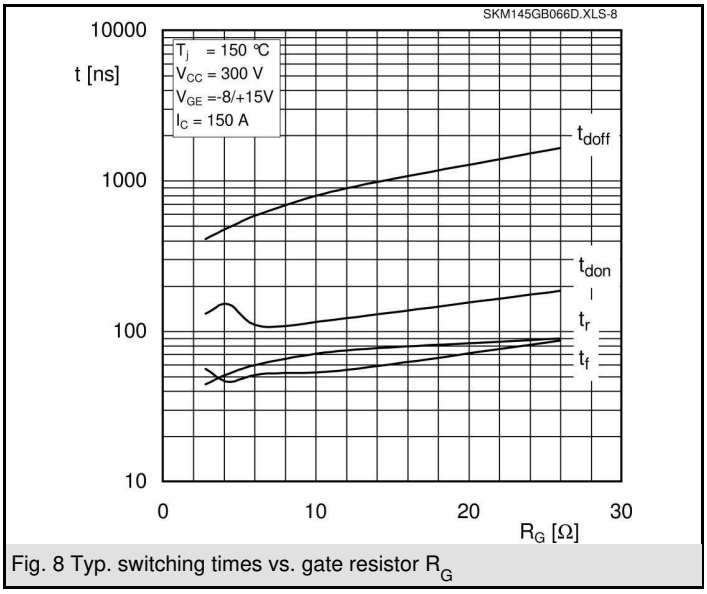


Fig. 8 Typ. switching times vs. gate resistor R_G

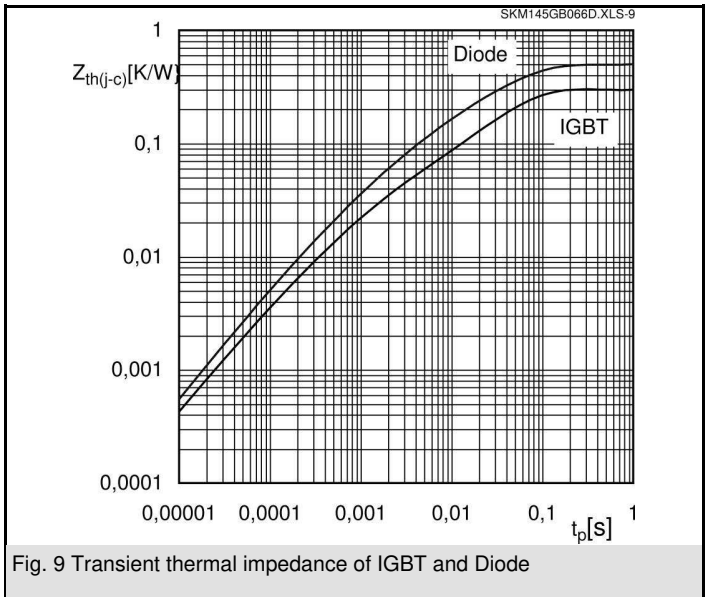


Fig. 9 Transient thermal impedance of IGBT and Diode

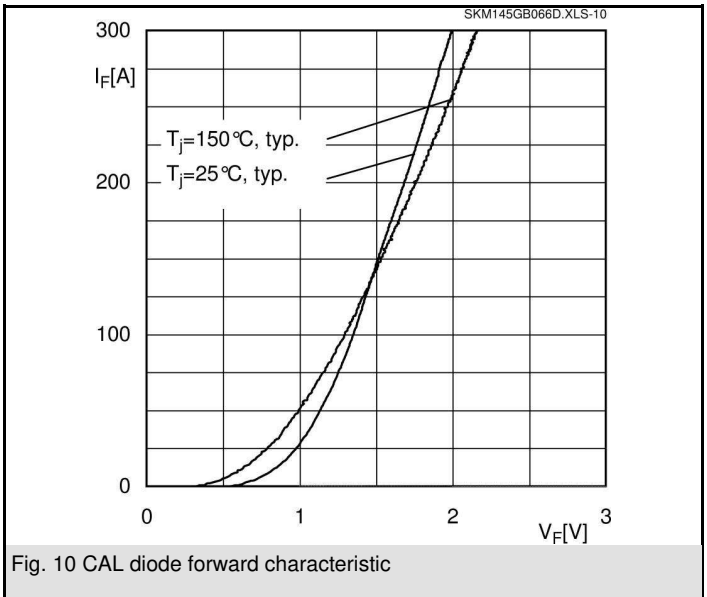


Fig. 10 CAL diode forward characteristic

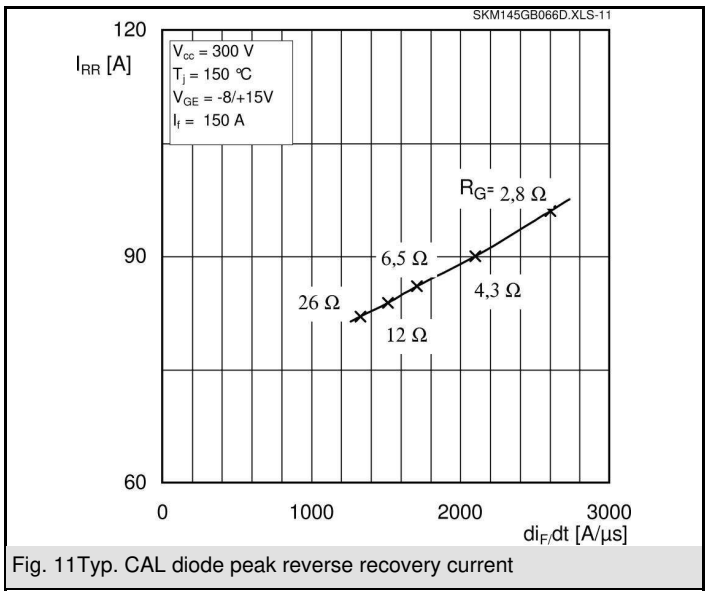


Fig. 11Typ. CAL diode peak reverse recovery current

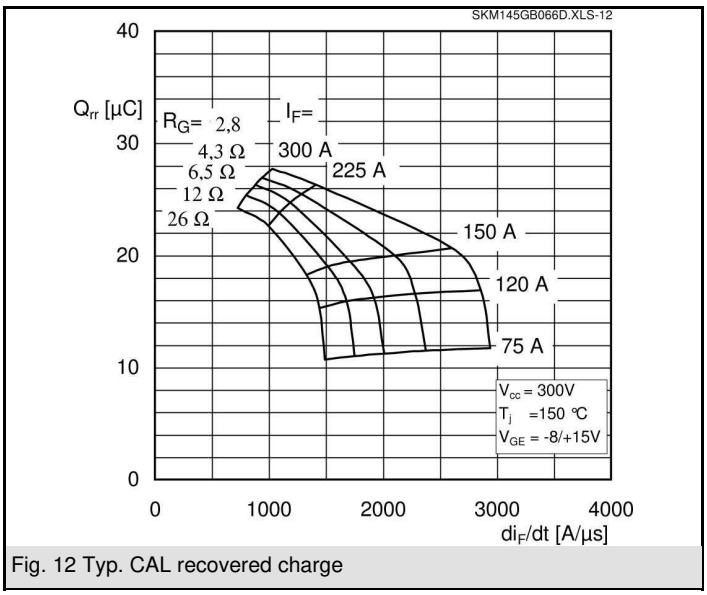
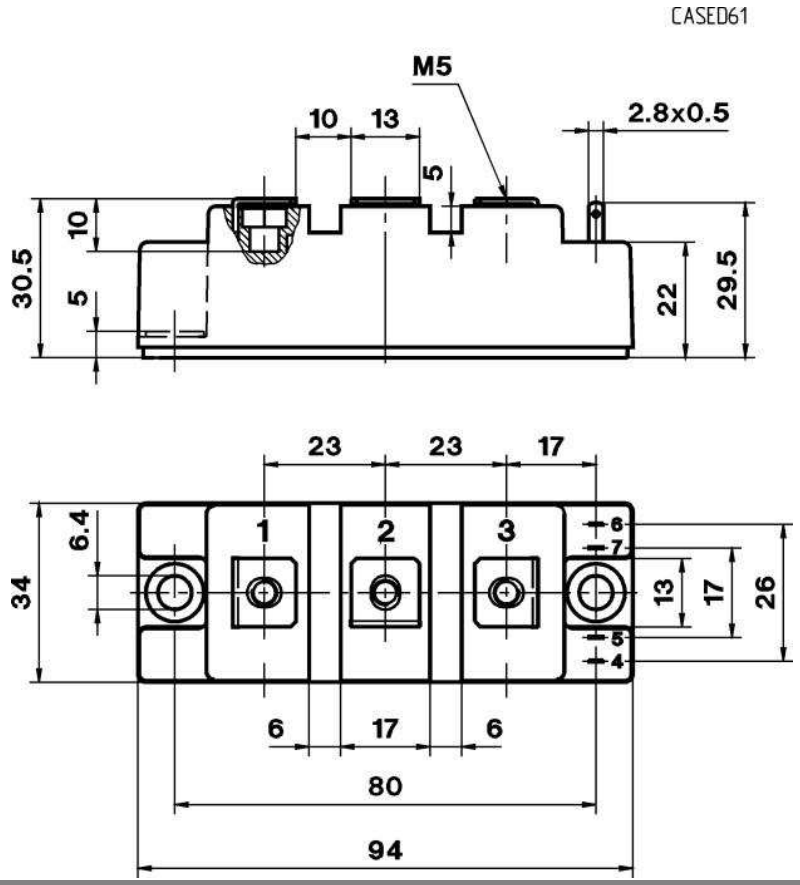


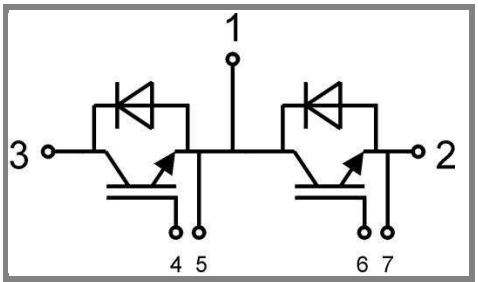
Fig. 12 Typ. CAL recovered charge

SKM 145GB066D

UL recognized, file no. E 63 532



Case D 61



GB Case D61

